

# Triak Z0103MN;ST;SMD;SOT223;1A;600V 3mA;RoHS



### Dane techniczne:

Nazwa: Z0103MN

Typ: Triak

Prąd przewodzenia: 1A Napięcie wsteczne: 600V

Prąd bramki: 3mA Obudowa: SOT223

Montaż: SMD Producent: ST

Product data sheet

### 1. Product profile

### 1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

#### 1.2 Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

### 1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 4; see Figure 5	-	-	8	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	1	Α



**4Q Triac** 

Table 1. Quick reference data ...continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
lgт	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ C}}$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ c}}$	-	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 9}}{^{\circ}\text{C}}$	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	5	mA

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2	4	T2T1
3	G	gate		`G <i>sym051</i>
4	T2	main terminal 2	1 2 3	
			SOT223 (SOT223)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
Z0103MN	SOT223	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; see Figure 3; see Figure 1; see Figure 2	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 4; see Figure 5	-	8	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	8.5	Α
I <sup>2</sup> t	I2t for fusing	$t_p = 10 \text{ ms}$ ; sine-wave pulse	-	0.32	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2+ G+	-	50	A/μs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu$ s; T2+ G-	-	50	A/μs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu s$ ; T2- G-	-	50	A/μs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.1 A/ $\mu s$ ; T2- G+	-	20	A/μs
I <sub>GM</sub>	peak gate current		-	1	Α
P <sub>GM</sub>	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

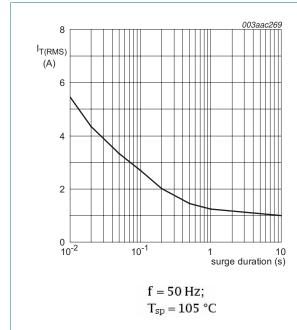


Fig 1. RMS on-state current as a function of surge duration; maximum values

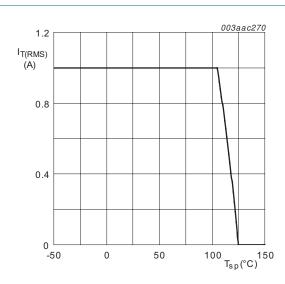


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

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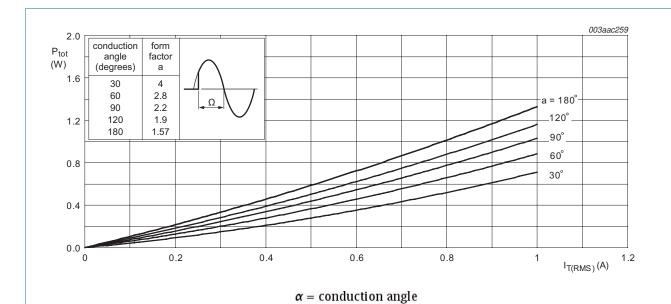


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

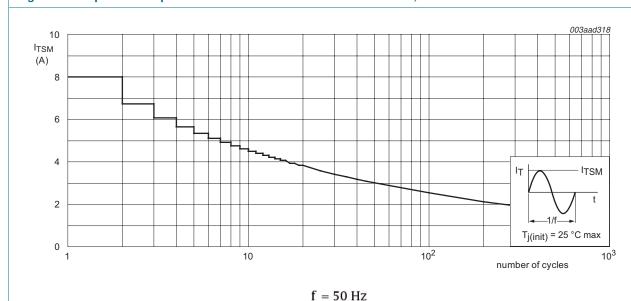
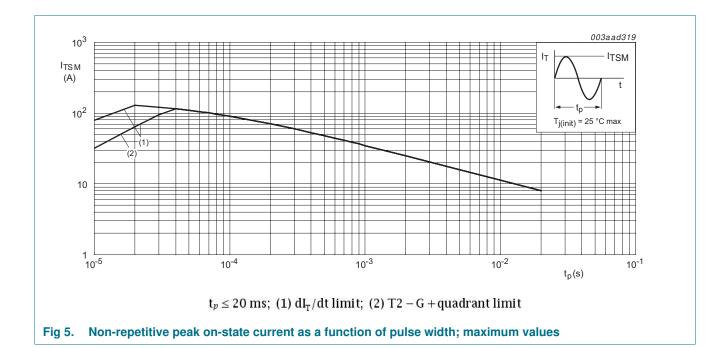


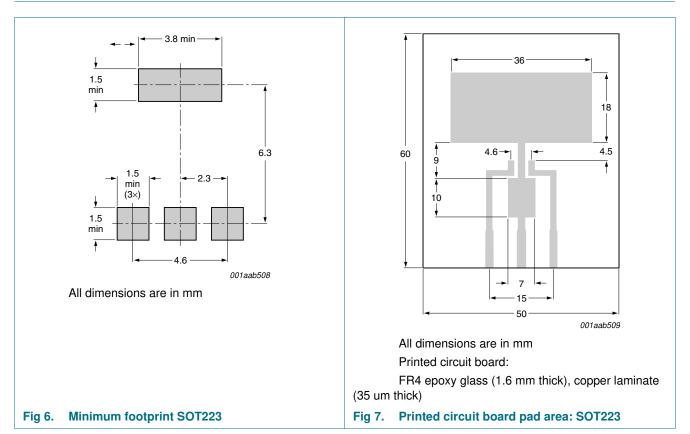
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



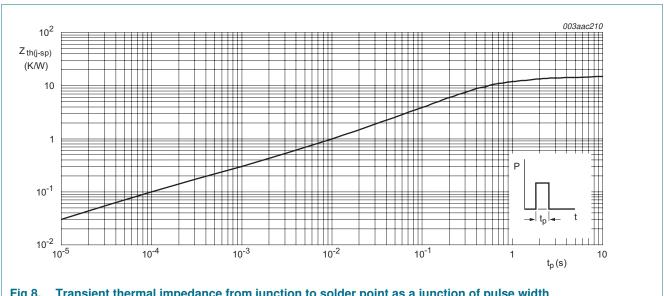
### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point	full cycle; see Figure 8	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; minimum footprint; see Figure 6	-	156	-	K/W
		full cycle; printed circuit board mounted; pad area; see Figure 7	-	70	-	K/W



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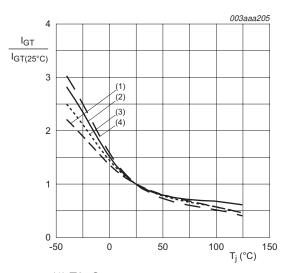


# 6. Characteristics

**Table 6. Characteristics** 

	Juanacteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 ^C;$ see Figure 9	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 \text{ °C};$ see Figure 9	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-}; T_j = 25 \text{ °C};$ see Figure 9	-	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; T_j = 25 ^{\circ}C;$ see Figure 9	-	-	5	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see Figure 10	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^C;$ see Figure 10	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 °C;$ see Figure 10	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2\text{- G+}; T_j = 25 \text{ °C};$ see Figure 10	-	-	7	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	-	7	mΑ
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.2	-	-	V
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	-	1.3	V
I <sub>D</sub>	off-state current	$V_D = 600 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	-	0.5	mΑ
Dynamic ch	aracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 110 °C; gate open circuit; exponential waveform; see Figure 13	10	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 \text{ °C};$ $dI_{com}/dt = 0.44 \text{ A/ms};$ gate open circuit	0.5	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 9. Normalized gate trigger current as a function of junction temperature

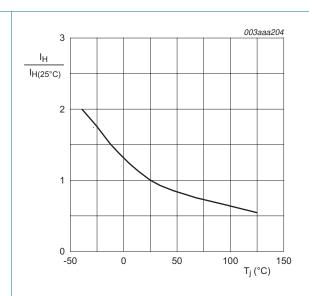
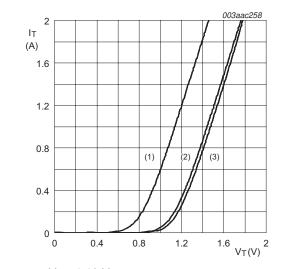


Fig 10. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$ 

 $R_s = 0.31 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig 11. On-state current as a function of on-state voltage

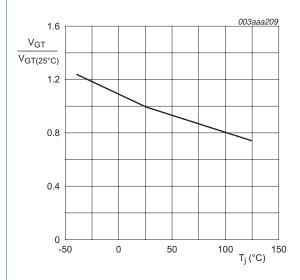


Fig 12. Normalized gate trigger voltage as a function of junction temperature

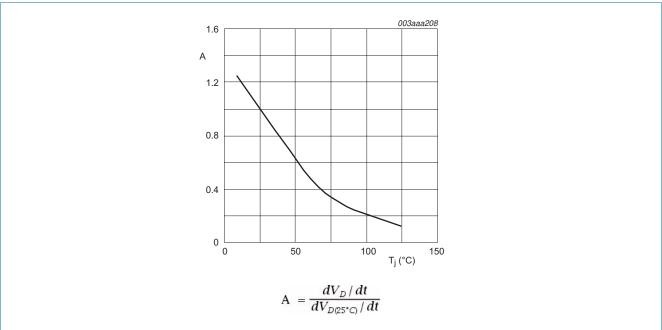


Fig 13. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

# 7. Package outline

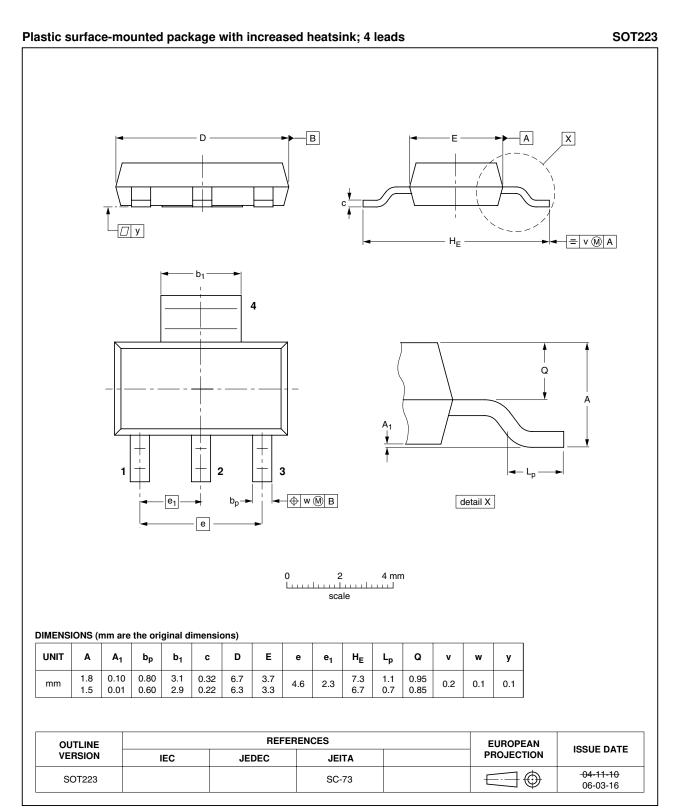


Fig 14. Package outline SOT223 (SOT223)

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# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0103MN v.5	20110321	Product data sheet	-	Z0103MN v.4
Modifications:	<ul> <li>Various chang</li> </ul>	es to content.		
Z0103MN v.4	20100906	Product data sheet	-	Z0103MN v.3

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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